GSM02P15

150V P-Channel MOSFET

General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

Features

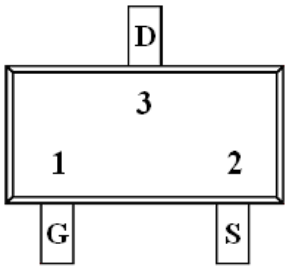
- -150V/-1A,RDS(ON)=750mΩ@VGS=-10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

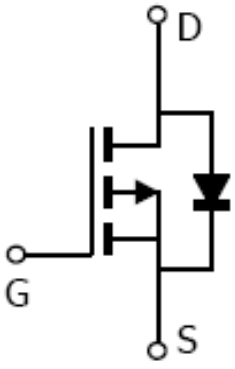
- Networking
- Load Switch
- LED applications

Packages & Pin Assignments

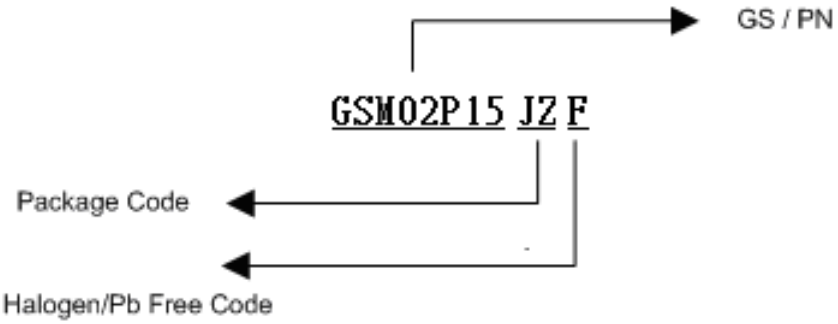
GSM02P15JZF(SOT-23)



1	Gate
2	Source
3	Drain

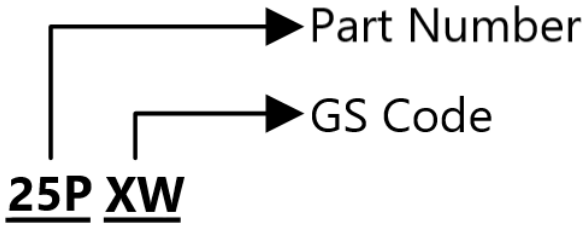


Ordering Information



Part Number	Package	Quantity Reel
GSM02P15JZF	SOT-23	3000 PCS

Marking Information



Absolute Maximum Ratings

(T_C=25ºC unless otherwise noted)

Symbol	Parameter	Typical	Unit
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate–Source Voltage	±20	V
I_D	Drain Current- Continuous (T_C=25ºC)	-1	A
	Drain Current- Continuous (T_C=100ºC)	-0.63	A
I_{DM}	Drain Current- Pulsed[1]	-4	A
P_D	Power Dissipation (T_C=25ºC)	1.56	W
	Power Dissipation –Derate above 25ºC	0.012	W/ºC
T_J	Operating Junction Temperature Range	-50 to 150	ºC
T_{STG}	Storage Temperature Range	-50 to 150	ºC
$R_{\theta JA}$	Thermal Resistance-Junction to ambient	80	ºC/W

Electrical Characteristics

(T_J=25ºC unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	-150	---	---	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS},I_D=-250uA	-2	-3	-4	
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V,V_{GS}=±20V	---	---	±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-150V, V_{GS}=0V, T_J=25ºC	---	---	-1	μA
		V_{DS}=-120V,V_{GS}=0V,T_J=125ºC	---	---	-10	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=-10V,I_D=-1A	---	650	800	mΩ
		V_{GS}=-6V,I_D=-0.5A	---	700	950	
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V, T_J=25ºC	---	---	-1	V
I_S	Continuous Source Current	V_{GS}=V_D=0V, Force Current	---	---	-1	A
I_{SM}	Pulsed Source Current		---	---	-2	A
g_{FS}	Forward Transconductance	V_{DS}=-10V,I_D=1A	---	2	---	S
R_g	Gate resistance	V_{DS}=0V, V_{GS}=0V, F=1MHz	---	30	60	Ω
Dynamic						
C_{iss}	Input Capacitance	V_{DS}=-25V, V_{GS}=0V, F=1MHz	---	430	700	pF
C_{oss}	Output Capacitance		---	38	60	
C_{rss}	Reverse Transfer Capacitance		---	28	56	
Q_g	Total Gate Charge[2,3]	V_{DS}=-75V, V_{GS}=10V, I_D=-1A	---	4.4	8	nC
Q_{gs}	Gate-Source Charge[2,3]		---	0.7	2	
Q_{gd}	Gate-Drain Charge[2,3]		---	1.5	3	
$t_{d(on)}$	Turn-On Time[2,3]	V_{DD}=-75V, V_{GS}=-10V, R_G=10Ω, I_D=-1A	---	12.5	20	ns
t_r			---	8.9	18	
$t_{d(off)}$	Turn-Off Time[2,3]		---	17.3	36	
t_f			---	11.5	24	

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Typical Performance Characteristics

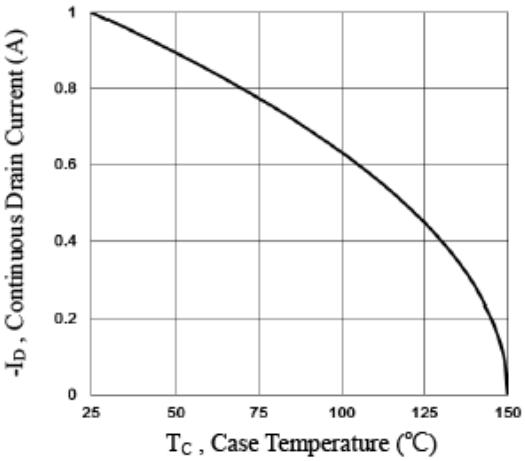


Fig.1 Continuous Drain Current vs. Tc

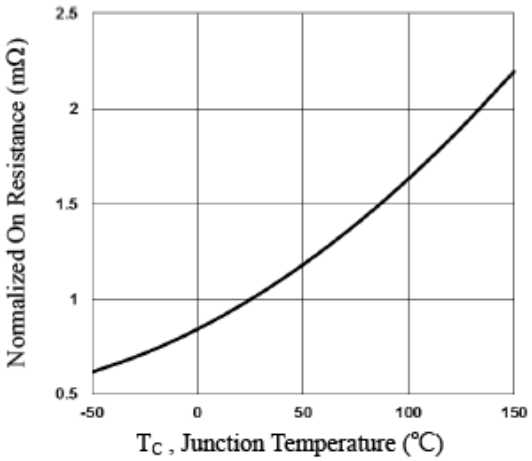


Fig.2 Continuous Drain Current vs. Tc

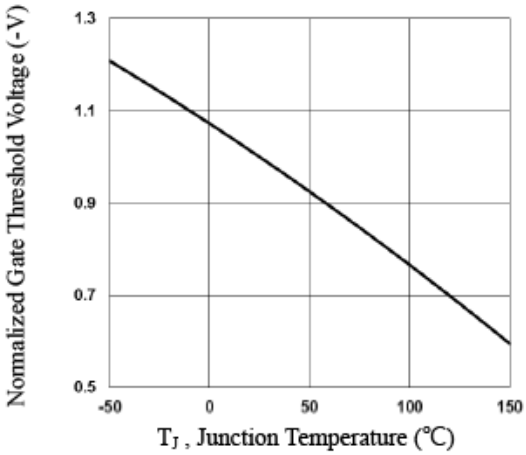


Fig.3 Normalized V_{th} vs. T_J

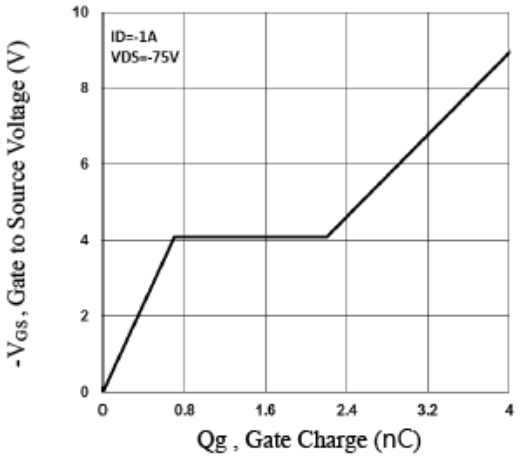


Fig.4 Gate Charge Waveform

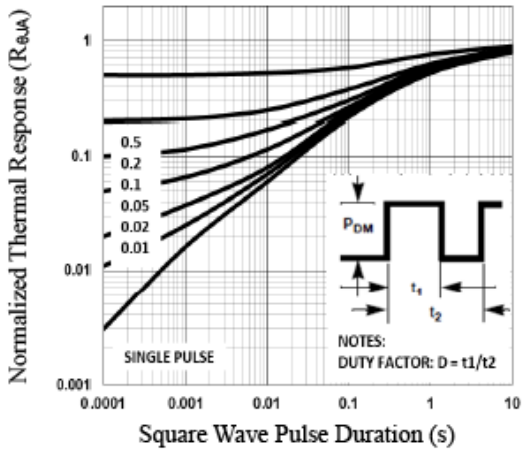


Fig.5 Normalized Transient Impedance

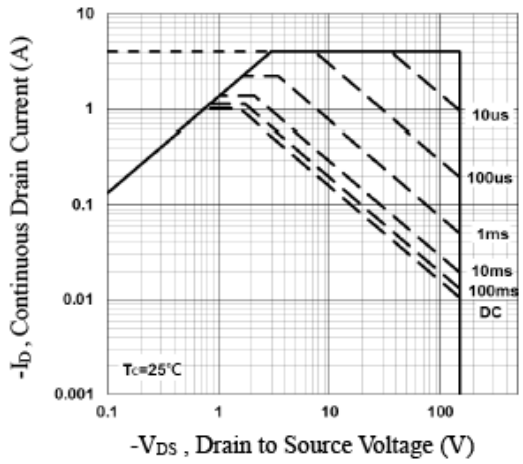


Fig.6 Maximum Safe Operation Area

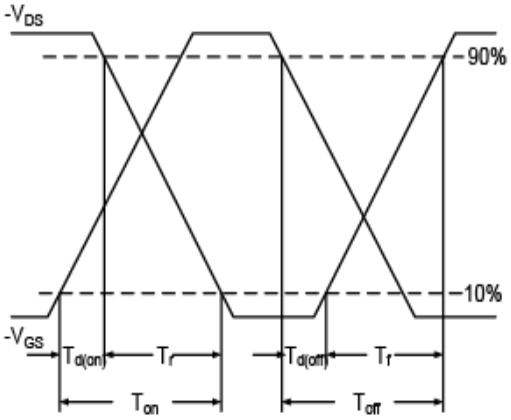


Fig.7 Switching Time Waveform

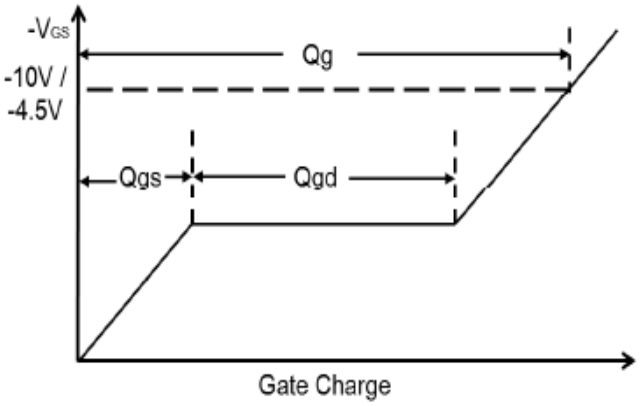
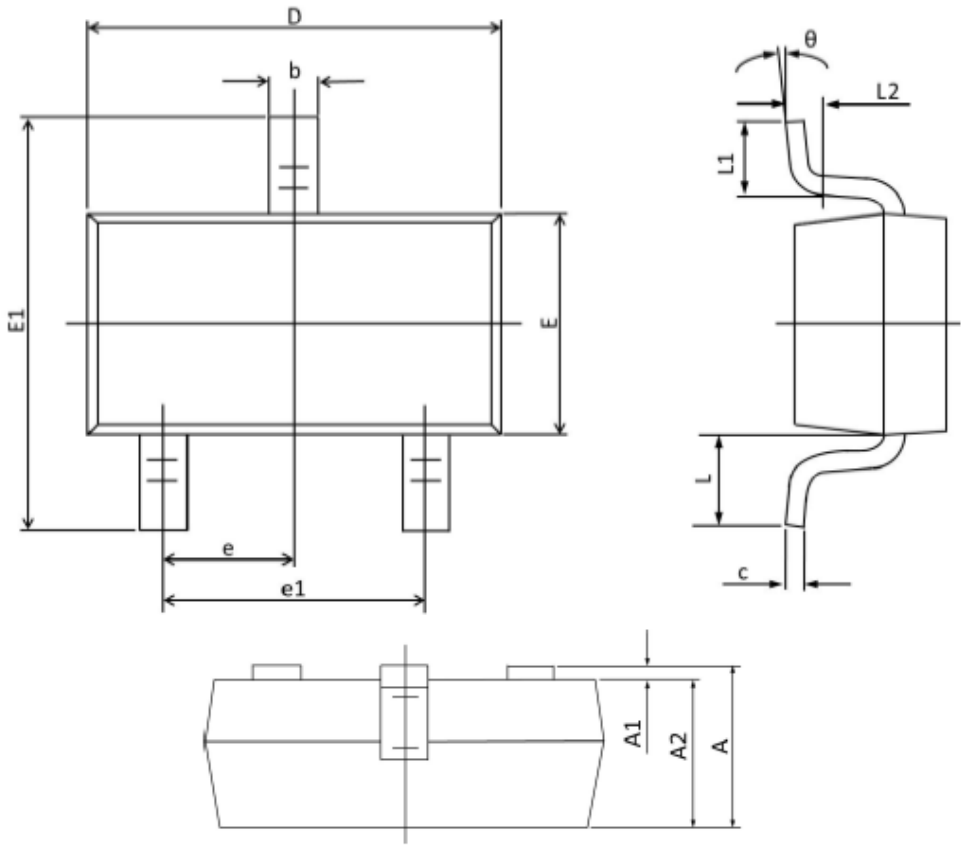


Fig.8 Gate Charge Waveform

Package Dimension

SOT-23



Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.008
D	2.800	3.000	0.110	0.006
E	1.200	1.400	0.047	0.118
E1	2.250	2.550	0.089	0.055
e	0.950 (TYP)		0.037 (TYP)	
e1	1.800	2.000	0.071	0.079
L	0.55(REF)		0.028 (REF)	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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